TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

### TLP627,TLP627-2,TLP627-4

## PROGRAMMABLE CONTROLLERS DC-OUTPUT MODULE TELECOMMUNICATION

The TOSHIBA TLP627,-2 and -4 consists of a gallium arsenide infrared emitting diode optically coupled to a darlington connected phototransistor which has an integral base-emitter resistor to optimize switching speed and elevated temperature characteristics.

The TLP627-2 offers two isolated channels in a eight lead plastic DIP, while the TLP627-4 provide four isolated channels per package.

Collector-Emitter Voltage : 300V(Min)
 Current Transfer Ratio : 1000%(Min)
 Isolation Voltage : 5000Vrms(Min)

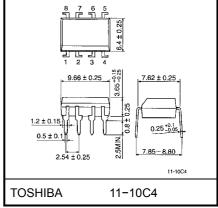
UL Recognized : UL1577, File No.E67349

	MADE IN JA	PAN	MADE IN THAILAND			
UL Recognized	E67349	*1	E152349	*1		
BSI Approved	7426, 7427	*2	7426, 7427	*2		

<sup>\*1</sup> UL1577

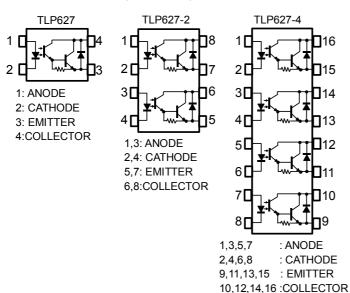
# Unit in mm 4 3 50 1.2 ± 0.15 0.5 ± 0.1 2.54 ± 0.25 TOSHIBA Unit in mm 7.62 ± 0.25 0.25 ± 0.05 11-5B2

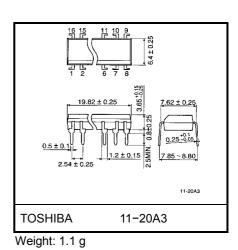
Weight: 0.26 g



Weight: 0.54 g

#### PIN CONFIGURATION (TOP VIEW)





<sup>\*2</sup> BS EN60065 : 1994,BS EN60950: 1992

#### MAXIMUM RATINGS(Ta=25°C)

	QUADACTERICTIO	OVANDOL	RATING		LINUT
	CHARACTERISTIC	SYMBOL	TLP627	TLP627-2 TLP627-4	- UNIT
	Forward Current	I <sub>F</sub>	60	50	mA
	Forward Current Derating	ΔI <sub>F</sub> /°C	-0.7(Ta≥39°C)	-0.5(Ta≥25°C)	mA /°C
	Pulse Forward Current	I <sub>FP</sub>	1(100µs pu	ılse,100pps)	Α
LED	Power Dissipation (1 Circuit)	P <sub>D</sub>	100	70	mW
	Power Dissipation Derating (Ta≥25°C,1 Circuit)	Δ P <sub>D</sub> /°C	-1.0	-0.7	mW /°C
	Reverse Voltage	V <sub>R</sub>	:	5	V
	Junction Temperature	Tj	1:	25	°C
	Collector-Emitter Voltage	V <sub>CEO</sub>	3	00	V
2	Emitter -Collector Voltage	V <sub>ECO</sub>	0	.3	٧
СТО	Collector Current	Ic	1	50	mA
ETECTOR	Collector Power Dissipation (1 Circuit)	Pc	150(*300)	100	mW
DI	Collector Power Dissipation Derating (Ta≥25°C,1 Circuit)	Δ P <sub>c</sub> /°C	-1.5(*-3.5)	-1.0	mW /°C
	Junction Temperature	Tj	1:	25	°C
Оре	rating Temperature Range	$T_{opr}$	-55	~100	°C
Stor	age Temperature Range	T <sub>stg</sub>	-55	~125	°C
Lead	d Soldering Temperature (10s)	T <sub>sold</sub>	260(1	l0sec)	°C
Tota	l Package Power Dissipation	P <sub>T</sub>	250(*320)	150	mW
Tota	ll Package Power Dissipation Derating (Ta≥25°C,1 Circuit)	Δ P <sub>T</sub> /°C	-2.5(*-3.2)	-1.5	mW /°C
Isola	ation Voltage (AC,1min. , R.H.≤60%) (Note1)	BVs	50	000	Vrms

\*IF=20mA Max

(Note1)Device considered a two terminal device : LED side pins Shorted together and DETECTOR side pins shorted together.

#### **RECOMMENDED OPERATING CONDITIONS**

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V <sub>CC</sub>	_	_	200	V
Forward Current	I <sub>F</sub>	_	16	25	mA
Collector Current	Ic	_	_	120	mA
Operating Temperature	T <sub>opr</sub>	-25	_	85	°C

#### INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta=25°C)

	CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
	Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 10 mA		1.15	1.3	V	
LED	Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 5 V		_	10	μΑ	
	Capacitance	Ст	V = 0 , f=1MHz	_	30	_	pF	
	Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	IC = 0.1mA	300	_	_	V	
DETECTOR	Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	IE = 0.1mA	0.3			V	
TEC	Collector Dark Current		Collector Dark Current Iceo	V <sub>CE</sub> = 200V	_	10	200	nA
Collector Dark Current I <sub>CEO</sub>		CEO	V <sub>CE</sub> = 200V , Ta = 85°C	_	_	20	μΑ	
	Capacitance Collector to Emitter	C <sub>CE</sub>	V=0 , f=1MHz		10	_	pF	

#### COUPLED ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I <sub>C</sub> /I <sub>F</sub>	I <sub>F</sub> =1mA , V <sub>CE</sub> =1V	1000	4000	_	%
Saturated CTR	I <sub>C</sub> /I <sub>F</sub> (sat)	I <sub>F</sub> =10mA , V <sub>CE</sub> =1V	500	_	_	%
Collector-Emitter	V <sub>CE</sub> (sat)	I <sub>C</sub> =10mA , I <sub>F</sub> =1mA	_	_	1.0	V
Saturation Voltage	V CE(Sat)	I <sub>C</sub> =100mA , I <sub>F</sub> =10mA	0.3	_	1.2	V

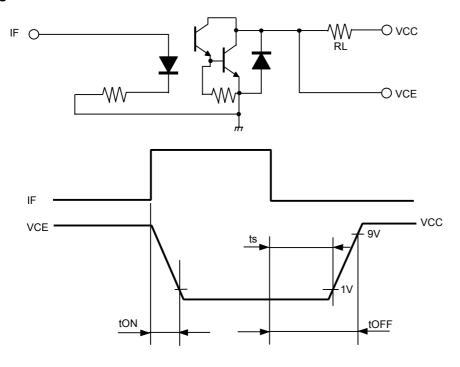
#### ISOLATION ELECTRICAL CHARACTERISTICS (Ta=25°C)

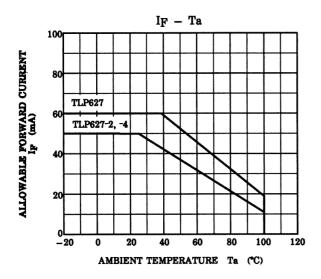
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance Input to Output	Cs	V <sub>S</sub> =0 , f=1MHz	_	8.0	_	pF
Isolation Resistance	Rs	V <sub>S</sub> =500V , R.H.≤60%	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
Isolation Voltage	_	AC, 1minute	5000	_	_	Vrms
		AC, 1second, in oil	_	10000	_	VIIIIS
		DC, 1 minute, in oil	_	10000	_	Vdc

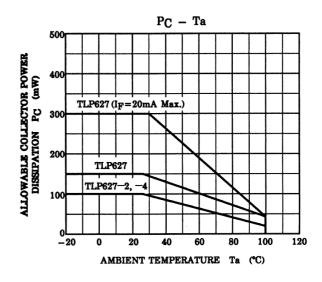
#### **SWITCHING CHARACTERISTICS (Ta=25°C)**

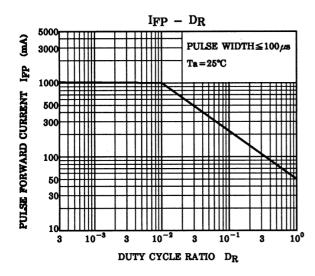
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	tr	)/ 40)/	_	40	_	
Fall Time	tf	V <sub>cc</sub> =10V I <sub>c</sub> =10mA	_	15	_	
Turn-on Time	ton	$R_L=100\Omega$	_	50	_	
Turn-off Time	toff		_	15	_	μs
Turn-on Time	tON	R <sub>L</sub> =180Ω (Fig.1) V <sub>CC</sub> =10V , I <sub>F</sub> =16mA	_	5	_	
Strage Time	ts		_	40	_	
Turn-off Time	tOFF		_	80	_	

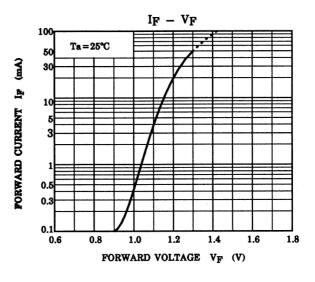
#### Fig.1 SWITCHING TIME TEST CIRCUIT

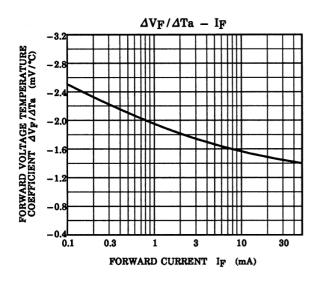


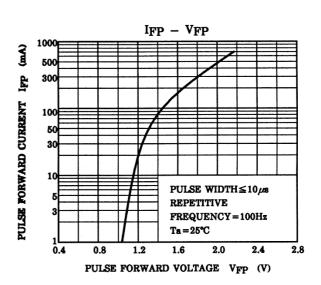




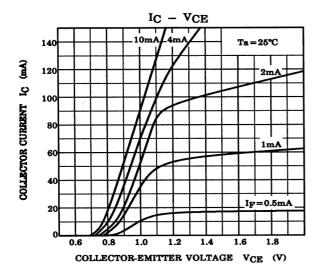


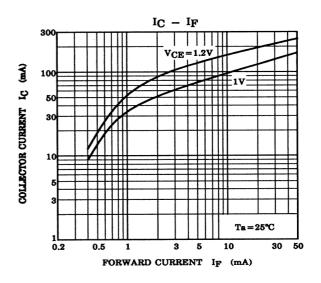


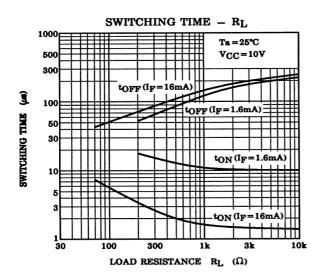


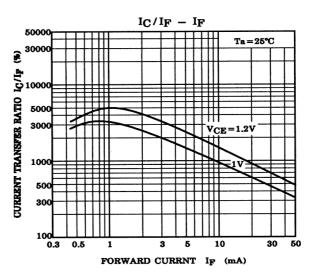


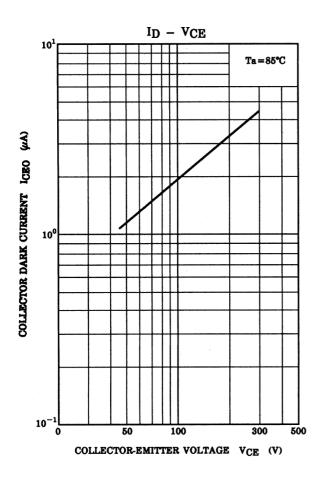
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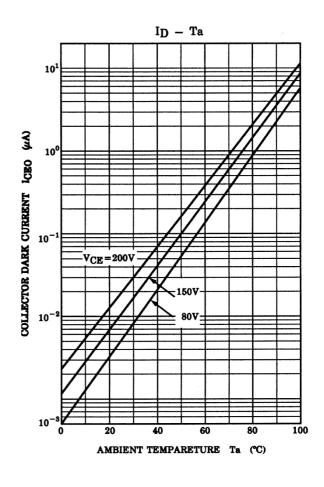


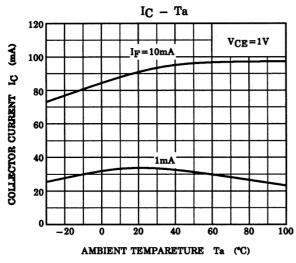


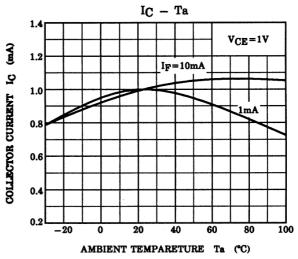












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